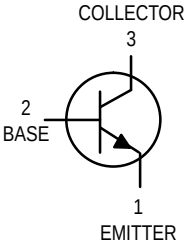
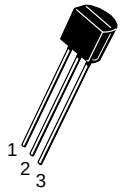
Amplifier Transistor
NPN Silicon

MPS6428





CASE 29–04, STYLE 1
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	50	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	50	—	Vdc
Collector–Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc)	I_{CES}	—	0.025	μA
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	0.01	μA
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	0.01	μA

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

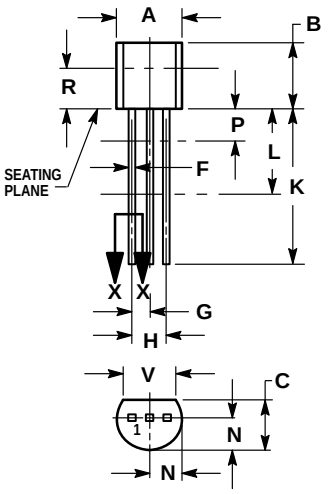
Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			—
(V_{CE} = 5.0 Vdc, I_C = 0.01 mAdc)		250	—	
(V_{CE} = 5.0 Vdc, I_C = 0.1 mAdc)		250	650	
(V_{CE} = 5.0 Vdc, I_C = 1.0 mAdc)		250	—	
(V_{CE} = 5.0 Vdc, I_C = 10 mAdc)		250	—	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 0.5 mAdc)		—	0.2	
(I_C = 100 mAdc, I_B = 5.0 mAdc)		—	0.6	
Base–Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	$V_{BE(on)}$	0.56	0.66	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product (I_C = 1.0 mAdc, V_{CE} = 5.0 V, f = 100 MHz)	f_T	100	700	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	3.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{ie}	3.0	30	kΩ
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{re}	2.0	20	X 10^{-4}
Small–Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	200	800	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{oe}	5.0	50	μmhos

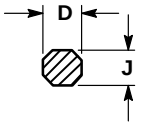
NOISE FIGURE/TOTAL NOISE VOLTAGE CHARACTERISTICS

	NF Max (1)	VT Max (1)	NF Max (2)	VT Max (2)	NF Max (3)	VT Max (3)	Unit	Unit
Noise Figure/Voltage (V_{CE} = 5.0 V, I_C = 0.1 mA, T_A = 25°C)	7.0	18.1	6.0	5700	3.5	4.3	dB	nV

1. R_S = 10 kΩ, BW = 1.0 Hz, f = 100 Hz
2. R_S = 50 kΩ, BW = 15.7 kHz, f = 10 Hz–10 kHz
3. R_S = 500 Ω, BW = 1.0 Hz, f = 10 Hz

PACKAGE DIMENSIONS





SECTION X–X

CASE 029–04
(TO–226AA)
ISSUE AD

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

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